



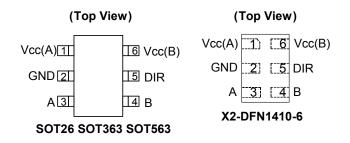
SINGLE BIT DUAL POWER SUPPLY TRANSLATING TRANSCEIVER WITH 3 STATE OUTPUTS

Description

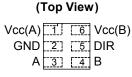
The 74LVC1T45 is a single bit, dual supply transceiver with 3-state outputs suitable for transmitting a single logic bit across different voltage domains. The A input/output pin is designed to track V_{CCA} while the B input/output tracks V_{CCB} . This arrangement allows for universal low-voltage translation between any voltages from 1.65V to 5.5V. The Direction pin (DIR) controls the direction of the transceiver and in a logic voltage related to V_{CCA} . When a high logic level is applied to DIR the A pin becomes an input and the B pin becomes the output. Conversely, the roles of A and B are reversed when DIR is asserted low.

The 3-state feature occurs when either of the power supply voltages are zero. This is also an loff feature and allows for the output to remain in a high impedance state with both power supplies at 0V, preventing and damaging backflow currents and providing power down electrical isolation up to 5.5V as not to interfere with any logic activity on pin A or B.

Pin Assignments







X2-DFN1010-6

Features

- Wide Supply Voltage Range:
 - V_{CC}(A): from 1.65V to 5.5V
 - V_{CC}(B): from 1.65V to 5.5V
- ± 24mA Output Drive at 3.3V
- CMOS Low Power Consumption 16µA Maximum I_{CC}
- High Noise Immunity (100mV Hysteresis Typical)
- I_{OFF} Supports Partial-Power-Down Mode Operation
- I_{OFF} Controlled by Either V_{CC} Being at 0 V
- Inputs Accept up to 5.5V
- ESD Protection Exceeds JESD 22
 - 200-V Machine Model (A115)
 - 2000-V Human Body Model (A114)
 - 1000 V Charged Device Model (C101)
- Latch-up Exceeds 100mA per JESD 78, Class I
- X2-DFN1409-6 Package Designed as a Direct Replacement for Chip Scale Packaging.
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Applications

- Voltage Level Translation
 Well suited to join logic types operating at different voltages
- Power Down Signal Isolation
 If either voltage domain is turned off the signal is isolated and there is no loading on signal lines
- Wide array of products such as:
 - Cell Phones, Tablets, E-Readers
 - PCs, Notebooks, Netbooks, Ultrabooks
 - Networking, Routers, Gateways
 - Computer Peripherals, Hard Drives, CD/DVD ROM
 - TV, DVD, DVR, Set-Top Box
 - Personal Navigation / GPS
 - MP3 Players, Cameras, Video Recorders

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

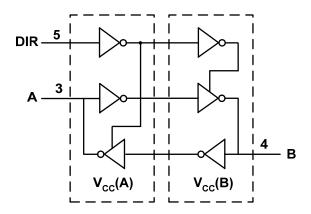
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Pin Descriptions

Pin Name	Pin	Function
VCC(A)	1	Supply for I/O pin A and reference for DIR
GND	2	Ground
A	3	Data Input/Output
В	4	Data Input/Output
DIR	5	Direction Control
VCC(B)	6	Supply for I/O pin B

Logic Diagram



Function Tables

Input DIR (Direction Pin)	Operation
L	B data to A output
Н	A data to B output

	Inputs		Outp	outs	
Α	В	A B			
*	L	L	L	*	
*	Н	L	Н	*	
L	*	Н	*	L	
Н	*	Н	*	Н	

^{*}Pin condition not applicable as defined by DIR.

Absolute Maximum Ratings (Note 4) (@T_A = +25°C, unless otherwise specified.)

Symbol	Parameter	Rating	Unit				
ESD HBM	Human Body Model ESD Protection	2	KV				
ESD CDM	Charged Device Model ESD Protection	1	KV				
ESD MM	Machine Model ESD Protection		200	V			
V _{CC} (A), V _{CC} (B)	Supply Voltage Range		-0.5 to +6.5	V			
VI	Input Voltage Range	nput Voltage Range					
Vo	Voltage Applied to Output in High Impedance or I _{OFF}	Voltage Applied to Output in High Impedance or I _{OFF} State					
\/	Voltage Applied to Output in High or Low State	A pin	-0.3 to V _{CC} (A) +0.5	V			
Vo	Voltage Applied to Output III High of Low State	B pin	-0.3 to V _{CC} (B) +0.5	V			
I _{IK}	Input Clamp Current V _I <0		-50	mA			
I _{OK}	Output Clamp Current		-50	mA			
Io	Continuous Output Current		±50	mA			
	Continuous Current Through Vcc or GND	±100	mA				
TJ	Operating Junction Temperature	-40 to +150	°C				
T _{STG}	Storage Temperature		-65 to +150	°C			

Note: 4. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.



Recommended Operating Conditions (Note 5) (@TA = +25°C, unless otherwise specified.)

Symbol	Param	eter	V _{CC} Inputs	V _{CC} Outputs	Min	Max	Units
V _{CC} (A)	On a nation of V	-14	-	-	1.65	5.5	V
V _{CC} (B)	Operating V	oitage	-	-	1.65	5.5	V
	High-Level I	nput	V _{CC} = 1.65V to 1.95V	-	0.65 X V _{CC(A)}	-	
.,,	Voltage Pin	•	V _{CC} = 2.3V to 2.7V	-	1.7	-	.,
V _{IH}	Referenced	to	V _{CC} = 3V to 3.6V	-	2	-	V
	V _{CC} (A)		V _{CC} = 4.5V to 5.5V	-	0.7 X V _{CC(A)}	_	
	Low-Level Ir	nput	V _{CC} = 1.65V to 1.95V	-	_	0.35 X V _{CC(A)}	
.,	Voltage Pin	•	V _{CC} = 2.3V to 2.7V	-	-	0.7	.,
VIL	Referenced	to	V _{CC} = 3V to 3.6V	-	-	0.8	V
	V _{CC} (A)		V _{CC} = 4.5V to 5.5V	-	-	0.3 X V _{CC(A)}	
	High-Level I	nput	V _{CC} = 1.65V to 1.95V	-	0.65 X V _{CC(B)}	_	
	Voltage Pin		V _{CC} = 2.3V to 2.7V	=	1.7	=	
V _{IH}	Referenced		V _{CC} = 3V to 3.6V	-	2	=	V
	V _{CC} (B)		V _{CC} = 4.5V to 5.5V	-	0.7 X V _{CC(B)}	=	
	Low-Level Ir	nput	V _{CC} = 1.65V to 1.95V	-	-	0.35 X V _{CC(B)}	
	Voltage Pin		V _{CC} = 2.3V to 2.7V	-	_	0.7	
V _{IL}	Referenced		V _{CC} = 3V to 3.6V	-	-	0.8	V
	V _{CC} (B)		V _{CC} = 4.5V to 5.5V	-	-	0.3 X V _{CC(B)}	
Vı	Input Voltag	е	-	-	0	5.5	V
Vo	Output Volta	age	-	-	0	Vcc	V
			-	V _{CC} = 1.65V to 1.95V	-	-4	
			-	V _{CC} = 2.3V to 2.7V	-	-8	
Іон	High-Level (Output	-	V _{CC} = 3V to 3.6V	-	-16	mA
	Current		-	V _{CC} = 4.5V to 5.5V	-	-24	
			-	V _{CC} = 1.65V to 1.95V	-	-32	
			-	V _{CC} = 2.3V to 2.7V	-	4	
			-	V _{CC} = 3V to 3.6V	-	8	
loL	Low-Level C	Output	-	V _{CC} = 4.5V to 5.5V	-	16	mA
	Current		-	V _{CC} = 1.65V to 1.95V	-	24	
			-	V _{CC} = 2.3V to 2.7V	-	32	
			V _{CC} = 1.65V to 1.95V	-	-	20	
	Input	Data	V _{CC} = 2.3V to 2.7V	-	-	20	
	Transition	Inputs	V _{CC} = 3V to 3.6V	-	_	10	
Δt/ΔV	Rise or Fall		V _{CC} = 4.5V to 5.5V	-	-	5	ns/V
	Rate	Control Inputs	V _{CC} = 1.65V to 5.5V	-	-	5	
TA	Operating F		-	-	-40	+125	°C

Note: 5. Unused inputs should be held at V_{CC} or Ground.



Electrical Characteristics (@T_A = +40°C to +85°C, unless otherwise specified.)

O. me le e l	Dame:	T = - 4	O a m ditti a :: -	V (A)	V (B)	T	_A = +25°	С	T _A = -40°C	to +85°C	
Symbol	Parameter	Test	Conditions	V _{CC} (A)	V _{CC} (B)	Min	Тур	Max	Min	Max	Unit
		I _{OH} = -100μA		1.65V to 5.5V	1.65V to 5.5V	_	_	_	V _{CC} – 0.1	=	
		I _{OH} = -4mA		1.65V	1.65V	_	_	_	1.2	=	
V_{OH}	High Level	I _{OH} = -8mA		2.3V	2.3V	_	_	_	1.9	=	V
	Output Voltage	I _{OH} = -24m/	١	3V	3V	-	-	-	2.4	=	
		I _{OH} = -32mA		4.5V	4.5V	-	-	-	3.8	-	
		I _{OL} = 100µA	1	1.65V to 5.5V	1.65V to 5.5V	-	_	-	-	0.1	
		I _{OL} = 4mA		1.65V	1.65V	1	-	-	-	0.45	
V_{OL}	Low-Level Output	I _{OL} = 8mA		2.3V	2.3V	1	-	-	-	0.3	V
	Voltage	I _{OL} = 24mA		3V	3V	1	-	-	-	0.55	
		I _{OL} = 32mA		4.5V	4.5V	1	-	-	-	0.55	
lı	Input Current	DIR	$V_I = V_{CC}(A)$ or GND	0 to 5.5V	0 to 5.5V	ı	-	± 1	_	± 2	μΑ
loff	Power Down	A Pin	V_1 or $V_0 = 0$ to	0	0V to 5.5V	=	=	± 1	-	± 2	μΑ
	Leakage Current	B Pin	5.5V	0 to 5.5V	0	_	-	± 1	-	± 2	
1	3-State Leakage	A Pin	$V_O = V_{CC}(A)$	1.65V to 5.5V	1.65V to 5.5V	-	-	± 1	=	± 2	
I_{OZ}	Current	B Pin	$V_O = V_{CC}(B)$	1.65V to 5.5V	1.65V to 5.5V	-	_	± 1	_	± 2	μΑ
		\/ E E\/	OND	1.65V to 5.5V	1.65V to 5.5V	-	_	_	-	3	
I_{CCA}	Supply Current	$V_1 = 5.5V$ or $I_0 = 0$	GND	5.5V	0	-	_	_	-	2	μΑ
		10 – 0		0	5.5V	-	-	-	=	-2	
		V _I = 5.5V oi	CND	1.65V to 5.5V	1.65V to 5.5V	-	-	-	_	3	
I_{CCB}	Supply Current	$I_{O} = 0$	GND	0V	5.5V	-	_	_	_	2	μΑ
		10 - 0		5.5V	0V	-	_	_	_	-2	
I _{CCA} + I _{CCB}	Supply Current	V _I = 5.5V or	GND I _O = 0	1.65V to 5.5V	1.65V to 5.5V	=	=	=	-	4	μΑ
Δl _{CCA}	Additional Supply	A pin	$= V_{CC}(A) -0.6V$ $IR = V_{CC}(A)$ $= open$	3V to 5.5V	3V to 5.5V					50	μA
ДICCA	Current	DIR= $V_{CC}(A)$ -0.6V A= $V_{CC}(A)$ or GND B = open		37 10 3.37	37 10 3.37					50	μΛ
ΔI _{CCB}	Additional Supply Current	$B = V_{CC}(B) -0.6V$ $DIR = GND$ $A = open$		3V to 5.5V	3V to 5.5V	-	_	_	_	50	μA
C _I	Input Capacitance	H)IR I	_I = V _{CC} (A) or ND	3.3V	3.3V	ı	2.5	-	_	ı	pF
C _{IO}	Input/Output Capacitance	1	_I = V _{CC} (A)/(B) or	3.3V	3.3V	_	6.0	_		_	pF



Electrical Characteristics (@T_A = +40°C to +125°C, unless otherwise specified.)

		_), (D)	T _A = -40°C	to +125°C	
Symbol	Parameter	Te	est Conditions	V _{CC} (A)	V _{CC} (B)	Min	Max	Unit
		I _{OH} = -100	AL	1.65V to 5.5V	1.65V to 5.5V	V _{CC} – 0.1	-	
	High Level	I _{OH} = -4m/	ı	1.65V	1.65V	1.2	-	
Voh	Output	I _{OH} = -8mA	ı	2.3V	2.3V	1.9	-	V
	Voltage	I _{OH} = -24m	A	3V	3V	2.4	-	
		I _{OH} = -32m	A	4.5V	4.5V	3.8	-	1
		I _{OL} = 100μ	A	1.65V to 5.5V	1.65V to 5.5V	_	0.1	
		I _{OL} = 4mA		1.65V	1.65V	_	0.45	
V_{OL}	High-Level	I _{OL} = 8mA		2.3V	2.3V	-	0.3	V
	Input Voltage	I _{OL} = 24m/	1	3V	3V	-	0.55	
		I _{OL} = 32m/	1	4.5V	4.5V	-	0.55	1
lı	Input Current	DIR	$V_I = V_{CC}(A)$ or GND	0 to 5.5V	0 to 5.5V	-	± 2	μA
l _{OFF}	Power Down Leakage	A Pin	V _I or V _O = 0 to 5.5V	0	1.65V to 5.5V	_	± 2	μA
1011	Current	B Pin	1701 10 0 10 0.01	1.65V to 5.5V	0V	=	± 2] "``
l _{OZ}	3-State Leakage	B Pin V _O =V _{CC} (E DIR = 0 V	V ₁ = 0 to 5.5V	1.65V to 5.5V	1.65V to 5.5V	-	± 2	μA
.02	Current	A Pin $V_O = V_{CC}(A)$ $DIR = V_{CC}(A)$	A)	1.65V to 5.5V	1.65V to 5.5V	-	± 2	μ, τ
	Supply	V _I = 5.5V (or GND	1.65V to 5.5V	1.65V to 5.5V	_	3	
I_{CCA}	Current	$I_0 = 0$	I OND	5.5V	0	_	2	μΑ
	Garrent	10 – 0		0	5.5V	_	-2	
	Supply	V _I = 5.5V (or GND	1.65V to 5.5V	1.65V to 5.5V	_	3	
I_{CCB}	Current	$I_0 = 0$	I OND	5.5V	0	_	2	μΑ
	Garrent	10 – 0		0	5.5V	_	-2	
I _{CCA} + I _{CCB}	Supply Current	$V_I = 5.5V \text{ o}$ $I_O = 0$	or GND	1.65V to 5.5V	1.65V to 5.5V	-	4	μА
Δ1-	Additional	A pin DII	V_{CC} (A) -0.6VR = V_{CC} (A)open	2\/ to 5 5\/	2)/ to 5 5)/		50	
ΔI _{CCA}	Supply Current	DIR A=	R= V _{CC} (A) -0.6V V _{CC} (A) or GND copen	3V to 5.5V	3V to 5.5V	_	50	μА
ΔI_{CCB}	Additional Supply Current	B pin DII	V _{CC} (B) -0.6V R = GND open	3V to 5.5V	3V to 5.5V		50	μА



Package Characteristics (V_{CC} = 3.3V, T_A = +25°C, unless otherwise specified.)

Symbol	Parameter	Package	Test Conditions	Min	Тур	Max	Unit
		SOT26		-	166	1	
		SOT363		-	371	-	
0	Thermal Resistance Junction-	SOT563	Note 6	_	290	_	°C/W
θ_{JA}	to-Ambient	DFN1410	Note 6	_	430	_	C/VV
		DFN1409		_	450	-	
	DFN1409 DFN1010 SOT26	DFN1010		_	510	-	
		SOT26		-	46	-	
		SOT363		_	143	-	
0	Thermal Resistance Junction SOT5	SOT563	Note 6	_	96	1	°C/W
⊕ ^{JC}	Alc Informative constants	DFN1410	Note 6	_	190	-	C/VV
		DFN1409		_	200	-	
		DFN1010		=	250	=	

Note:

Switching Characteristics (V_{CC} (A) = 1.8V \pm 0.15V, T_A = -40°C to +85°C, see Figure 1)

Parameter	From (Input)	To (Output)		= 1.8V 15V		= 2.5V .2V		= 3.3V .3V		3)= 5V).5V	Unit
	(iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pLH}	A	В	3	17.7	2.2	10.3	1.7	8.3	1.4	7.5	ns
t _{pHL}	_ A	В	2.8	14.3	2.2	8.5	1.8	8.1	1.7	7.5	115
t _{pLH}	В	Α	3	17.7	2.3	16	2.1	15.5	1.9	15.1	ns
t _{pHL}		_ ^	2.8	14.3	2.1	12.9	2	12.6	1.8	12.2	115
t _{pHZ}	DIR	Α	5.2	19.4	4.8	18.5	4.7	18.4	5.1	17.1	
t _{pLZ}	DIK	_ ^	2.3	10.5	2.1	10.5	2.4	10.7	3.1	10.9	ns
t _{pHZ}	DIR	В	6.4	21.9	4.9	11.5	4.6	10.3	2.8	8.2	ns
t _{pLZ}	DIK	В	4.2	17	3.7	9.6	3.3	8.8	2.4	8.0	115
t _р zн	DIR	Α	_	33.7	-	25.2	_	23.9	-	21.5	no
t _{pZL}	DIK	^	_	36.2	_	24.4	_	22.9	_	20.4	ns
t _{pZH}	DIR	В	_	28.2	_	20.8	_	19	_	18.1	no
t _{pZL}	DIK	В	_	33.7	-	27	_	25.5	-	24.1	ns

Switching Characteristics (cont.) (V_{CC} (A) = 2.5V \pm 0.2V, T_A = -40°C to +85°C, see Figure 1)

Parameter	From (Input)	To (Output)		= 1.8V 15V		V _{CC} (B) = 2.5V ±0.2V		V _{CC} (B) = 3.3V ±0.3V		V _{CC} (B) = 5V ±0.5V	
	(iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pLH}	A	В	2.3	16	1.5	8.5	1.3	6.4	1.1	5.1	ns
t _{pHL}	A	ь	2.1	12.9	1.4	7.5	1.3	5.4	0.9	4.6	115
t _{pLH}	В	Α	2.2	10.3	1.5	8.5	1.4	8	1	7.5	no
t _{pHL}	В	A	2.2	8.5	1.4	7.5	1.3	7	0.9	6.2	ns
t _{pHZ}	DIR	А	3	8.1	3.1	8.1	2.8	8.1	3.2	8.1	ns
t _{pLZ}	DIK	4	1.3	5.9	1.3	5.9	1.3	5.9	1	5.8	115
t _{pHZ}	DIR	В	5.5	23.7	3.6	11.4	3.5	10.2	2.4	7.1	no
t _{pLZ}	DIK	ь	3.9	18.9	3.2	9.6	2.8	8.4	1.8	5.3	ns
t _{pZH}	NIB	۸	_	29.2	_	18.1	_	16.4	_	12.8	ns
t _{pZL}	DIR	R A	_	32.2	_	18.9	_	17.2	_	13.3	115
t _{рZH}	DIR	В	_	21.9	_	14.4	-	12.3	_	10.9	ns

^{6.} Test condition for SOT26, SOT363, DFN1410, DFN1409 and DFN1010: Device mounted on FR-4 substrate PC board, 2oz copper with minimum recommended pad layout.



Switching Characteristics (cont.) (V_{CC} (A) = 3.3V \pm 0.3V, T_A = -40°C to +85°C, see Figure 1)

Parameter	From (Input)	To (Output)		= 1.8V 15V		= 2.5V .2V		= 3.3V .3V	V _{CC} (B) = 5V ±0.5V		Unit
	(iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pLH}	A	В	2.1	15.5	1.4	8	0.7	5.8	0.7	4.4	no
t _{pHL}	^	Ь	2	12.6	1.3	7	8.0	5	0.7	4	ns
t _{pLH}	В	Α	1.7	8.3	1.3	6.4	0.7	5.8	0.6	5.4	no
t _{pHL}		A	1.8	7.1	1.3	5.4	0.8	5	0.7	4.5	ns
t _{pHZ}	DIR	^	2.9	7.3	3	7.3	2.8	7.3	3.4	7.3	20
t _{pLZ}	DIR	Α	1.8	5.6	1.6	5.6	2.2	5.7	2.2	5.7	ns
t _{pHZ}	DIR	В	4.0	20.5	3.5	10.1	2.9	8.8	2.4	6.8	no
t _{pLZ}	DIK	Ь	3.3	14.5	2.9	7.8	2.4	7.1	1.7	4.9	ns
t _{pZH}	DID	^	_	22.8	-	14.2	_	12.9	_	10.3	20
t _{pZL}	DIR	R A	-	27.6	_	15.5	_	13.8	_	11.3	ns
t _{pZH}	DIR	В	_	21.1	_	13.6	_	11.5	_	10.1	no
t _{pZL}	DIR	В	_	19.9	-	14.3	_	12.3	-	11.3	ns

Switching Characteristics (cont.) (V_{CC} (A) = 5V ± 0.5V, T_A = -40°C to +85°C, see Figure 1)

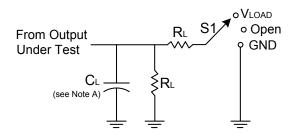
Parameter	From (Input)	To (Output)		= 1.8V 15V	V _{CC} (B) = 2.5V ±0.2V		V _{CC} (B) = 3.3V ±0.3V		V _{CC} (B)= 5V ±0.5V		Unit
	(iliput)	(Output)	Min	Max	Min	Max	Min	Max	Min	Max	
t _{pLH}	A	В	1.9	15.1	1	7.5	0.6	5.4	0.5	3.9	ns
t _{pHL}		В	1.8	12.2	0.9	6.2	0.7	4.5	0.5	3.5	115
t _{pLH}	В	Α	1.4	8.5	1	5.1	0.7	4.4	0.5	3.9	20
t _{pHL}		A	1.7	8.5	0.9	4.6	0.7	4	0.5	3.5	ns
t _{pHZ}	DIR	Α	2.1	5.4	2.2	5.4	2.2	5.5	2.2	5.4	20
t _{pLZ}	DIK	A	0.9	3.8	1	3.8	1	3.7	0.9	3.7	ns
t _{pHZ}	DIR	В	4.8	20.2	2.5	9.8	1	8.5	2.2	6.5	20
t _{pLZ}	DIK	Ь	4.2	14.8	2.5	7.4	2.5	7	1.6	4.5	ns
t _{pZH}	DID	^	-	22	-	12.5	-	11.4	-	8.4	20
t _{pZL}	DIR	Α	_	27.2	_	14.4	-	12.5	_	10	ns
t _{pZH}	DIR	В	=	18.9	=	11.3	=	9.1	-	7.6	ns

Operating Characteristics (T_A = +25°C, unless otherwise specified.)

Parameter Power Dissipation Capacitance		Test Conditions	$V_{CC}(A) = V_{CC}(B) = 1.8V$	$V_{CC}(A) = V_{CC}(B) = 2.5V$	$V_{CC}(A) = V_{CC}(B) = 3.3V$	$V_{CC}(A) = V_{CC}(B) = 5V$	Unit
l ower bis	i ower bissipation capacitance		Тур	Тур	Тур	Тур	
	A- input, B- output	$C_L = 0 pF$	3	4	4	4	
C _{pd} (A)	B- input, A- output	f = 10 MHz tr = tf = 1 ns	18	19	20	21	pF
	A- input, B- output	C _L = 0 pF	18	19	20	21	
C _{pd} (B)	B- input, A- output	f = 10 MHz tr = tf = 1 ns	3	4	4	4	pF

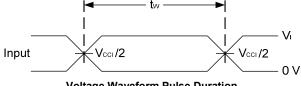


Parameter Measurement Information

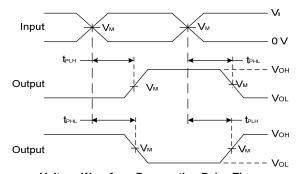


TEST	S1	
t _{PLH} /t _{PHL}	Open	
t _{PLZ} /t _{PZL}	Vload	
t _{PHZ} /t _{PZH}	GND	

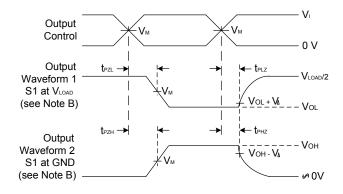
V	Inputs		, , , , , , , , , , , , , , , , , , ,				
V _{CC}	VI	t _r /t _f	V _M	V_{LOAD}	CL	R_L	V Δ
1.8V±0.15V	V _{CCI}	≤2ns	V _{CCO} /2	2 X V _{CCO}	15pF	2ΚΩ	0.15V
2.5V±0.2V	V _{CC}	≤2ns	V _{CCO} /2	2 X V _{CCO}	15pF	2ΚΩ	0.15V
3.3V±0.3V	3V	≤2.5ns	V _{CCO} /2	2 X V _{CCO}	15pF	2ΚΩ	0.3V
5V±0.5V	V _{CC}	≤2.5ns	V _{CCO} /2	2 X V _{CCO}	15pF	2ΚΩ	0.3V



Voltage Waveform Pulse Duration



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs



Voltage Waveform Enable and Disable Times Low and High Level Enabling

October 2014

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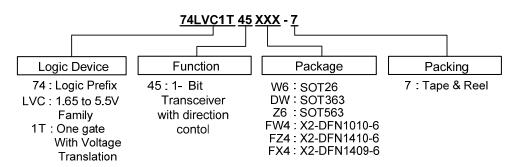
Figure 1 Load Circuit and Voltage Waveforms

Notes: A. Includes test lead and test apparatus capacitance.

- B. Waveform 1 is for an output with input set up as a low and device coming out or into 3-state via DIR control. Waveform 2 is for an output with input set up as a high and device coming out or into 3-state via DIR control.
- C. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
- D. t_{PLZ} and t_{PHZ} are the same as $t_{dis.}$
- E. t_{PZL} and t_{PZH} are the same as t_{EN.}
- F. t_{PLH} and t_{PHL} are the same as $t_{\text{PD.}}$
- G. V_{CCI} is the V_{CC} associated with the input.
- F. V_{CCO} is the V_{CC} associated with the output.



Ordering Information

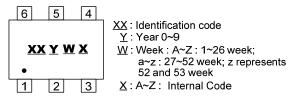


Part Number	Package Code Packa	Dookoging	7" Tape and Reel (Note 7)	
Part Number		Packaging	Quantity	Part Number Suffix
74LVC1T45W6-7	W6	SOT26	3000/Tape & Reel	-7
74LVC1T45DW-7	DW	SOT363	3000/Tape & Reel	-7
74LVC1T45Z6-7	Z6	SOT563	4000/Tape & Reel	-7
74LVC1T45FW4-7	FW4	X2-DFN1010-6	5000/Tape & Reel	-7
74LVC1T45FZ4-7	FZ4	X2-DFN1410-6	5000/Tape & Reel	-7
74LVC1T45FX4-7	FX4	X2-DFN1409-6	5000/Tape & Reel	-7

Note: 8. The taping orientation is located on our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

(1) SOT363, SOT563



Part Number	Package	Identification Code
74LVC1T45W6	SOT26	TT
74LVC1T45DW	SOT363	TR
74LVC1T45Z6	SOT563	TS

(2) X2-DFN1010-6, X2-DFN1410-6, and X2-DFN1409-6

(Top View)

XX XX : Identification Code Y : Year : 0~0

Year: 0~9

W: Week: A~Z: 1~26 week; a~z: 27~52 week; z represents

52 and 53 week X: A~Z: Internal code

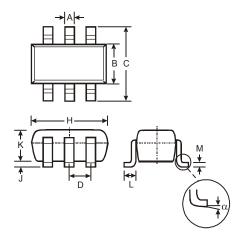
Part Number	Package	Identification Code
74LVC1T45FW4	X2-DFN1010-6	TR
74LVC1T45FX4	X2-DFN1409-6	TT
74LVC1T45FZ4	X2-DFN1410-6	TS



Package Outline Dimensions (All dimensions in mm.)

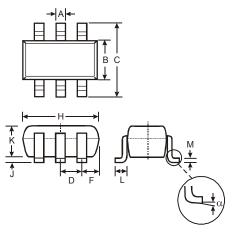
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

(1) Package Type: SOT26



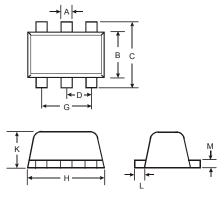
	SOT26					
Dim	Min	Max	Тур			
Α	0.35	0.50	0.38			
В	1.50	1.70	1.60			
С	2.70	3.00	2.80			
D			0.95			
Н	2.90	3.10	3.00			
J	0.013	0.10	0.05			
K	1.00	1.30	1.10			
L	0.35	0.55	0.40			
M	0.10	0.20	0.15			
α	0°	8°	_			
All D	imensi	ons in	mm			

(2) Package Type: SOT363



	SOT363					
Dim	Min	Max				
Α	0.10	0.30				
В	1.15	1.35				
С	2.00	2.20				
D	0.65 Typ					
F	0.40	0.45				
Н	1.80	2.20				
J	0	0.10				
K	0.90	1.00				
L	0.25	0.40				
М	0.10	0.22				
α	0°	8°				
All Di	mensions	in mm				

(3) Package Type: SOT563



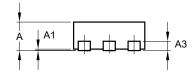
	SOT563					
Dim	Min	Max	Тур			
Α	0.15	0.30	0.20			
В	1.10	1.25	1.20			
С	1.55	1.70	1.60			
D	-	1	0.50			
G	0.90	1.10	1.00			
Н	1.50	1.70	1.60			
K	0.55	0.60	0.60			
L	0.10	0.30	0.20			
М	0.10	0.18	0.11			
All	All Dimensions in mm					

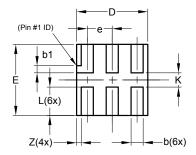


Package Outline Dimensions (cont.) (All dimensions in mm.)

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.

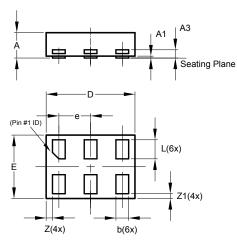
(4) Package Type X2-DFN1010-6





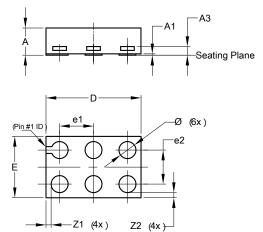
X2-DFN1010-6 Dim Max Min Тур 0.40 0.39 Α 0.00 0.05 **A**1 0.02 А3 0.13 0.14 0.20 0.17 b b1 0.05 0.15 0.10 0.95 1.00 D 1.05 Ε 0.95 1.05 1.00 0.35 е L 0.35 0.45 0.40 K 0.15 0.065 Ζ All Dimensions in mm

(5) Package Type: X2-DFN1410-6



X2-DFN1410-6					
Dim	Min	Max	Тур		
Α	_	0.40	0.39		
A1	0.00	0.05	0.02		
A3	_	_	0.13		
b	0.15	0.25	0.20		
D	1.35	1.45	1.40		
Е	0.95	1.05	1.00		
е			0.50		
L	0.25	0.35	0.30		
Z	_	_	0.10		
Z 1	0.045	0.105	0.075		
All Dimensions in mm					

(6) Package Type: X2-DFN1409-6 CHIP SCALE ALTERNATIVE



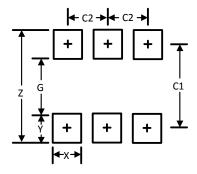
X2-DFN1409-6					
Dim	Min	Max	Тур		
Α	ı	0.40	0.39		
A1	0	0.05	0.02		
A3	-	-	0.13		
Ø	0.20	0.30	0.25		
D	1.35	1.45	1.40		
Е	0.85	0.95	0.90		
e1	ı	1	0.50		
e2	-	-	0.50		
Z1	-	-	0.075		
Z2	ı	-	0.075		
All D	All Dimensions in mm				



Suggested Pad Layout

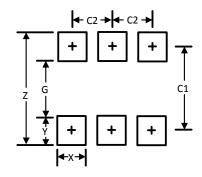
Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

(1) Package Type: SOT26



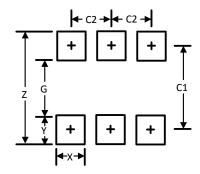
Dimensions	Value (in mm)
Z	3.20
G	1.60
х	0.55
Y	0.80
C1	2.40
C2	0.95

(2) Package Type: SOT363



Dimensions	Value (in mm)
Z	2.5
G	1.3
Х	0.42
Υ	0.6
C1	1.9
C2	0.65

(3) Package Type: SOT563



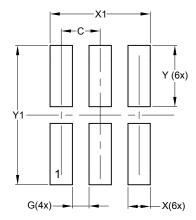
Dimensions	Value (in mm)
Z	2.2
G	1.2
X	0.375
Y	0.5
C1	1.7
C2	0.5



Suggested Pad Layout (cont.)

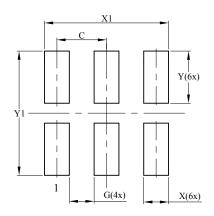
Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

(4) Package Type X2-DFN1010-6



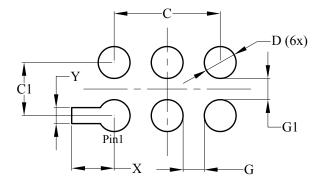
Dimensions	Value (in mm)
С	0.350
G	0.150
X	0.200
X1	0.900
Y	0.550
Y1	1.250

(5) Package Type: X2-DFN1410-6



Dimensions	Value (in mm)
С	0.500
G	0.250
Х	0.250
X1	1.250
Υ	0.525
Y1	1.250

(6) Package Type: X2-DFN1409-6



Dimensions	Value
	(in mm)
С	1.000
C1	0.500
D	0.300
G	0.200
G1	0.200
X	0.400
Υ	0.150



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